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**ABSTRACT OF THE DISCLOSURE**

The invention relates to a field-effect microelectronic device, as well as the method of production thereof. The device includes a substrate (700) as well as at least one improved structure (702) capable of forming one or more transistor channels. This structure, formed by a plurality of bars stacked on the substrate, can make it possible to save space in the integration of field-effect transistors as well as to improve the performance thereof.

Figure 7.